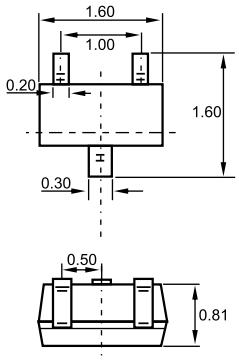
BAW56T/BAV70T/BAV99T

Switching Diode



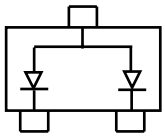
SOT-523



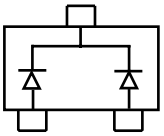
Dimensions in inches and (millimeters)

Features

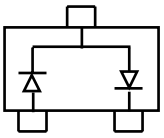
- ✧ Fast Switching Speed
- ✧ For General Purpose Switching Applications
- ✧ High Conductance



BAW56T Marking: JD



BAV70T Marking: JJ



BAV99T Marking: JE

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	85	V
Forward current	I_O	75	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65~150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	I_R= 1μA	85		V
Reverse voltage leakage current	I_{R1}	V_R=75V		2	μA
	I_{R2}	V_R=25V		0.03	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Diode capacitance	C_D	V_R=0 f=1MHz		1.5	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA I_{rr}=0.1×I_R,R_L=100Ω		4	nS

Typical Characteristics

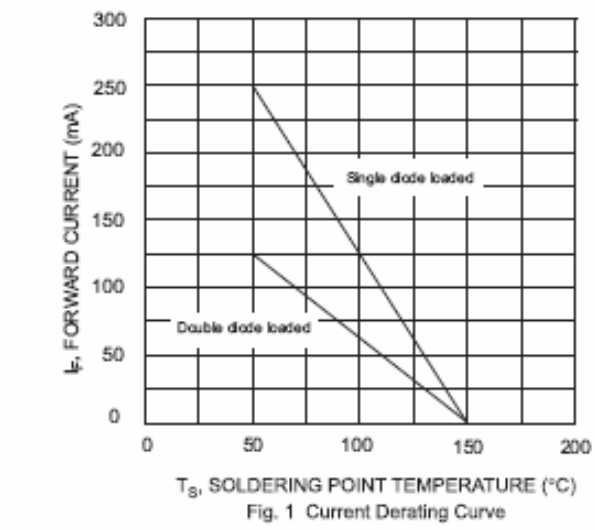


Fig. 1 Current Derating Curve

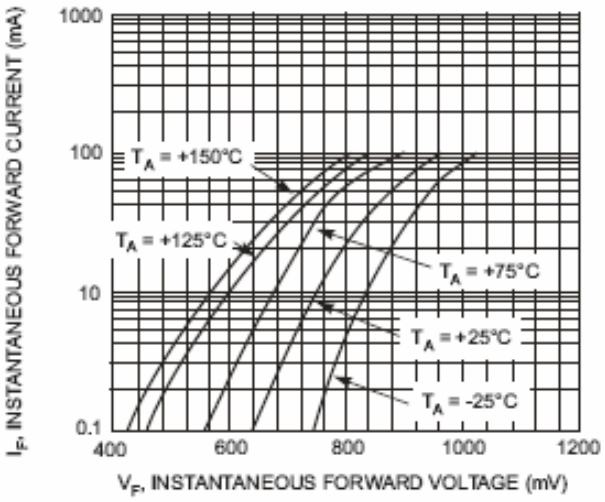


Fig. 2, Typical Forward Characteristics

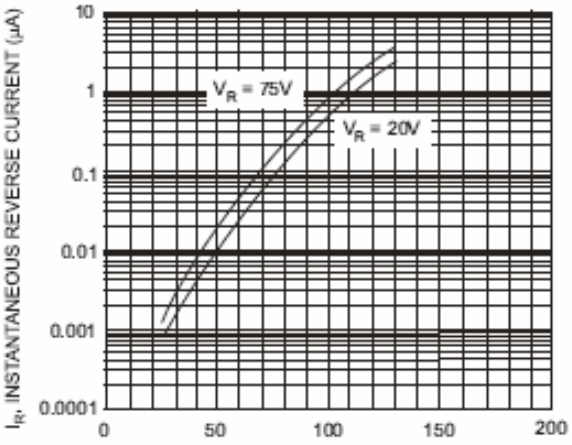


Fig. 3, Typical Reverse Characteristics